

## N-Channel 60 V (D-S) 175 °C MOSFET

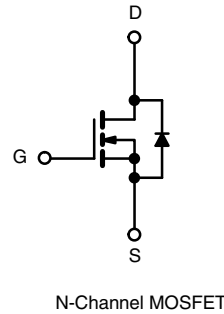
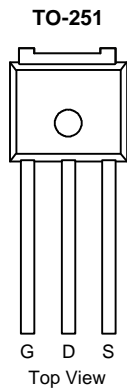
PRODUCT SUMMARY	
V <sub>DS</sub> (V)	60
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.006
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V	0.009
I <sub>D</sub> (A)	70
Configuration	Single

### FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>g</sub> and UIS Tested



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	60	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> = 25 °C	70	
		T <sub>C</sub> = 125 °C	56	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	100	A	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	290		
Single Pulse Avalanche Current	I <sub>AS</sub>	75		
Single Pulse Avalanche Energy	E <sub>AS</sub>	L = 0.1 mH	101	mJ
Maximum Power Dissipation <sup>b</sup>			T <sub>C</sub> = 25 °C	
		T <sub>C</sub> = 125 °C	45	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.1	

### Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

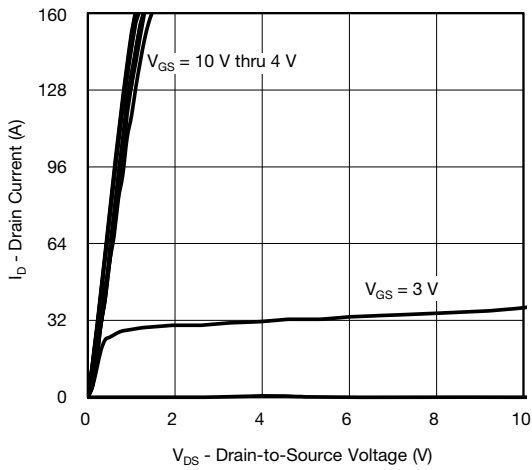
SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.5	2.0	2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	50	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 25\text{ A}$	-	-	0.006	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 25\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.017	
		$V_{GS} = 10\text{ V}$	$I_D = 25\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.049	
		$V_{GS} = 4.5\text{ V}$	$I_D = 20\text{ A}$	-	-	0.009	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		-	177	-	S
<b>Dynamic<sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	4844	6060	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	441	555	
Reverse Transfer Capacitance	$C_{rss}$			-	200	250	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 50\text{ A}$	-	82	125	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	14.5	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	13.5	-	
Gate Resistance	$R_g$	f = 1 MHz		1	2	3	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	14	21	ns
Rise Time <sup>c</sup>	$t_r$			-	5	8	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			-	41	62	
Fall Time <sup>c</sup>	$t_f$			-	7	11	
<b>Source-Drain Diode Ratings and Characteristics<sup>b</sup></b>							
Pulsed Current <sup>a</sup>	$I_{SM}$			-	-	290	A
Forward Voltage	$V_{SD}$	$I_F = 50\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.5	V

### Notes

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

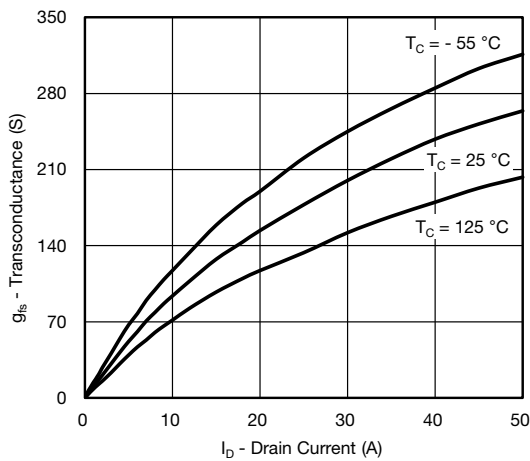
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



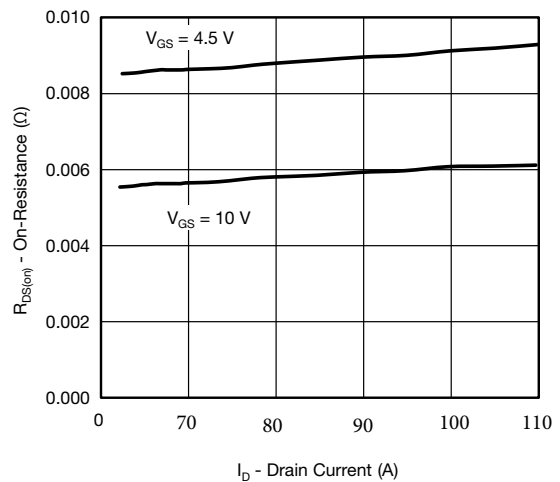
**Output Characteristics**



**Transfer Characteristics**



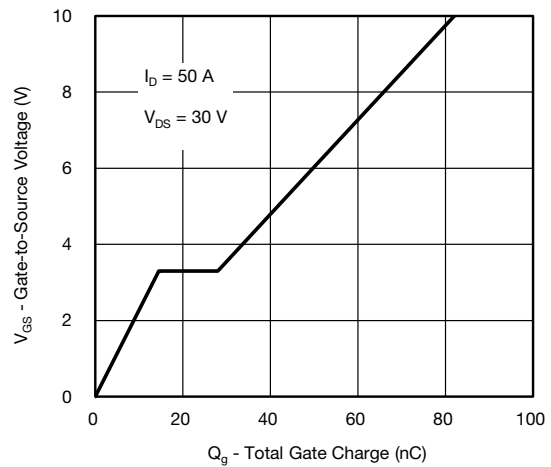
**Transconductance**



**On-Resistance vs. Drain Current**

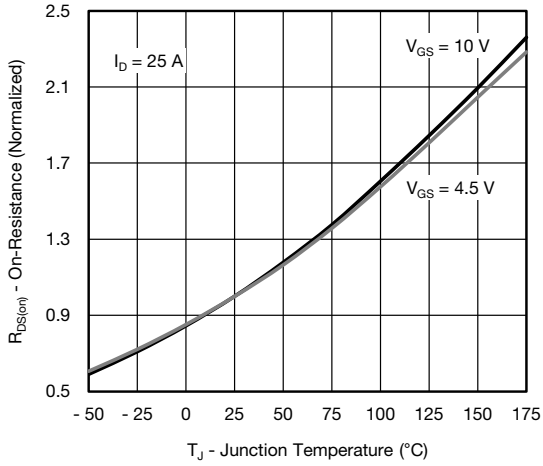


**Capacitance**

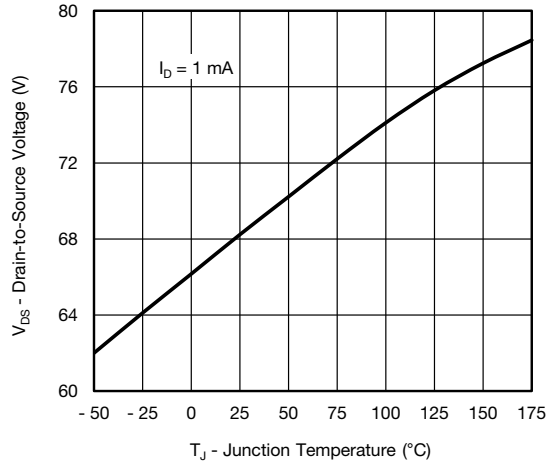


**Gate Charge**

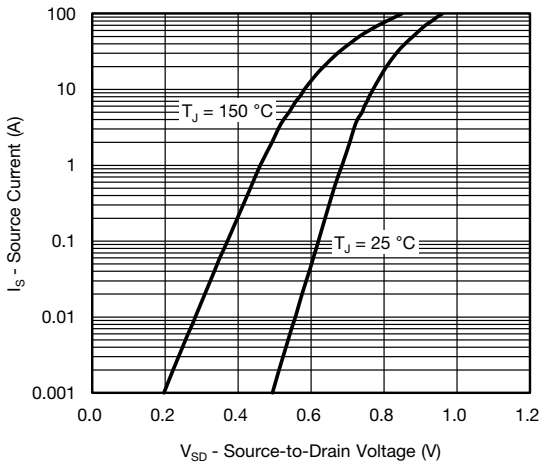
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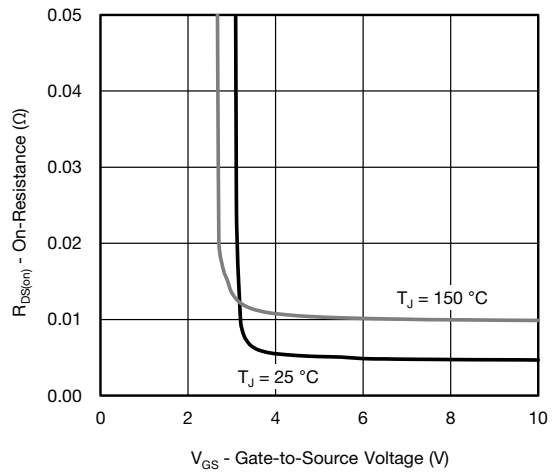
**On-Resistance vs. Junction Temperature**



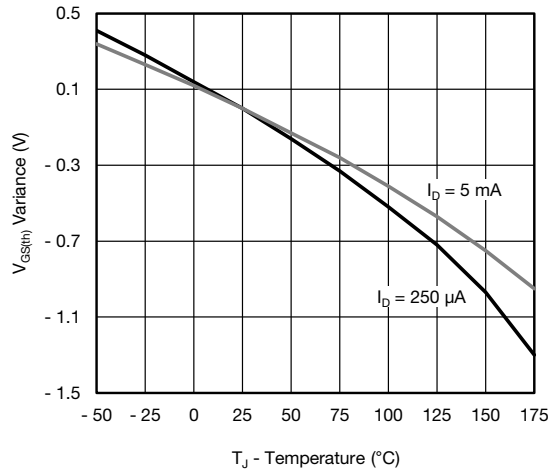
**Drain Source Breakdown vs. Junction Temperature**



**Source Drain Diode Forward Voltage**

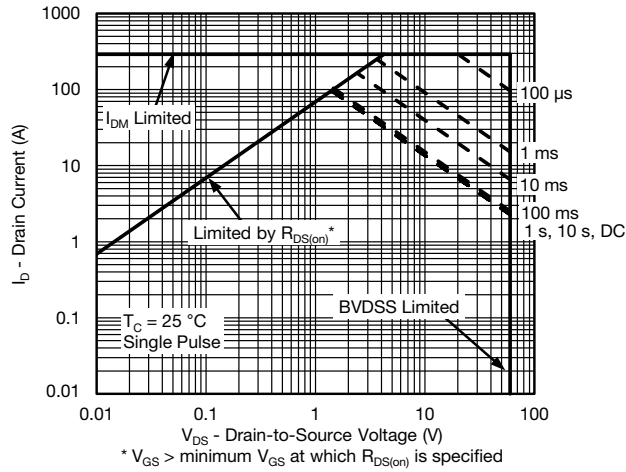


**On-Resistance vs. Gate-to-Source Voltage**

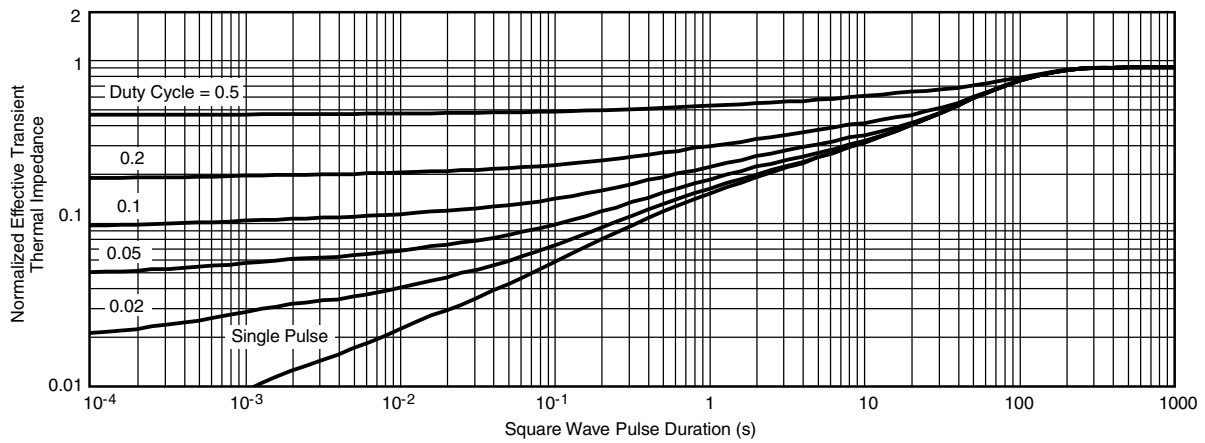


**Threshold Voltage**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

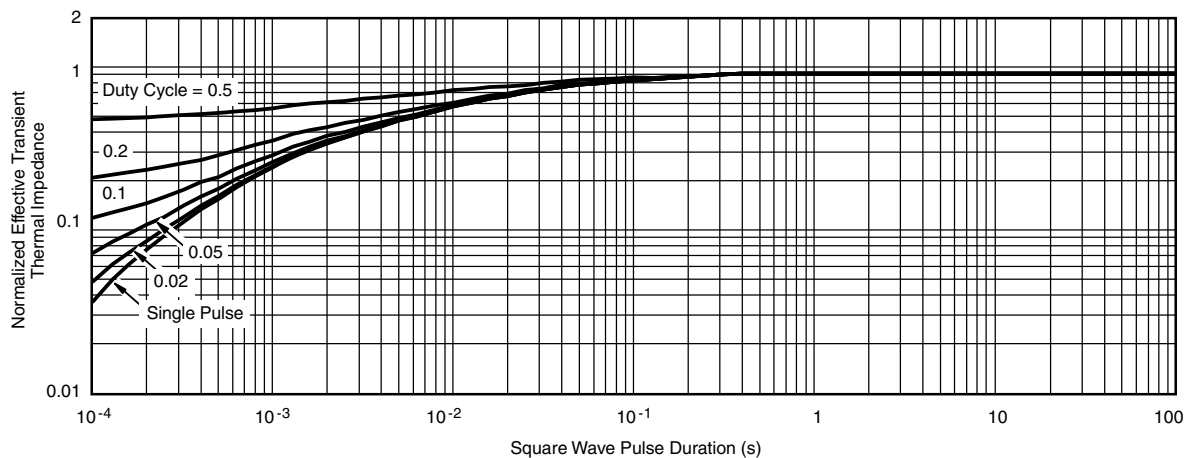


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

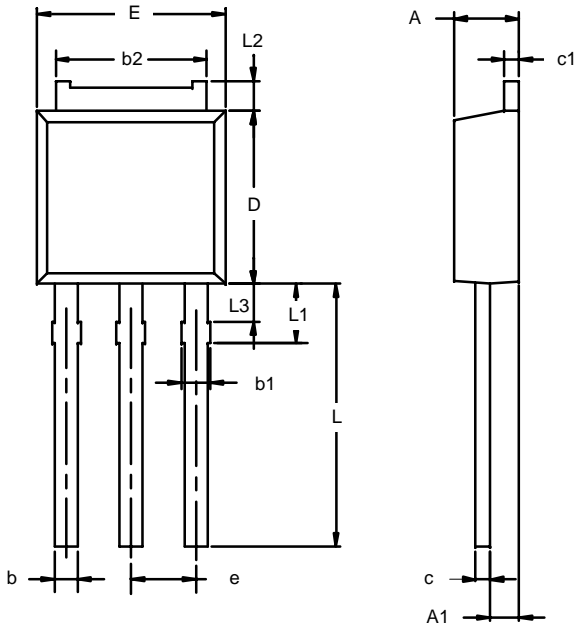


**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

**TO-251AA**



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	3.89	9.53	0.153	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060

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